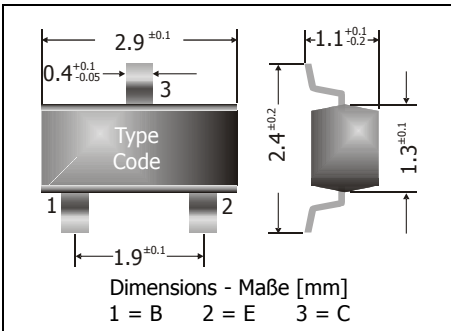


BCV26

PNP Surface Mount Darlington Si-Epi-Planar Transistors
Si-Epi-Planar Darlington-Transistoren für die Oberflächenmontage PNP

Version 2015-05-12



Power dissipation – Verlustleistung 200 mW
 Plastic case SOT-23
 Kunststoffgehäuse (TO-236)
 Weight approx. – Gewicht ca. 0.01 g
 Plastic material has UL classification 94V-0
 Gehäusematerial UL94V-0 klassifiziert
 Standard packaging taped and reeled
 Standard Lieferform getupet auf Rolle



Maximum ratings (T_A = 25°C)

Grenzwerte (T_A = 25°C)

			BCV26
Collector-Emitter-volt. – Kollektor-Emitter-Spannung	B open	- V _{CEO}	30 V
Collector-Base-voltage – Kollektor-Basis-Spannung	E open	- V _{CBO}	40 V
Emitter-Base-voltage – Emitter-Basis-Spannung	C open	- V _{EBO}	10 V
Power dissipation – Verlustleistung		P _{tot}	200 mW ¹⁾
Collector current – Kollektorstrom (dc)		- I _C	500 mA
Junction temperature – Sperrschichttemperatur		T _j	-55...+150°C
Storage temperature – Lagerungstemperatur		T _s	-55...+150°C

Characteristics (T_j = 25°C)

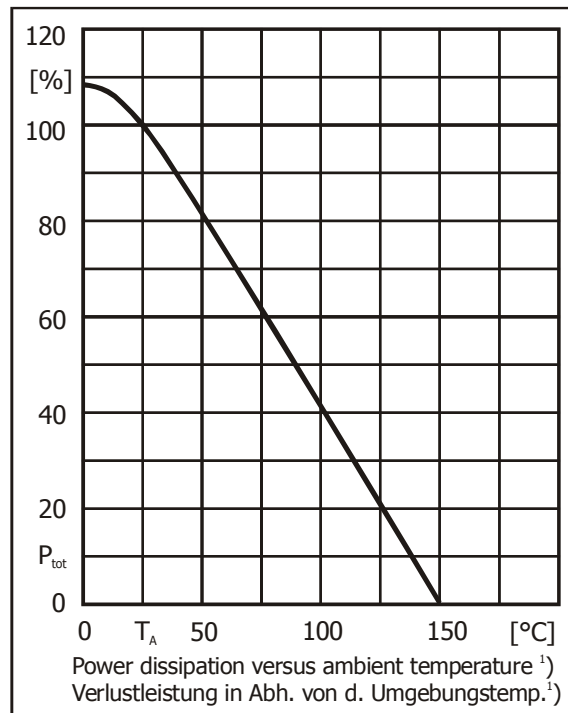
Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis ²⁾				
- V _{CE} = 5 V, - I _C = 1 mA	h _{FE}	4000	–	–
- V _{CE} = 5 V, - I _C = 10 mA	h _{FE}	10000	–	–
- V _{CE} = 5 V, - I _C = 100 mA	h _{FE}	20000	–	–
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg. ²⁾				
- I _C = 100 mA, - I _B = 0.1 mA	- V _{CEsat}	–	–	1.0 V
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung ²⁾				
- I _C = 100 mA, - I _B = 0.1 mA	- V _{BEsat}	–	–	1.5 V

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
 Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss
 2 Tested with pulses t_p = 300 μs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 μs, Schaltverhältnis ≤ 2%

Characteristics ($T_j = 25^\circ\text{C}$)
Kennwerte ($T_j = 25^\circ\text{C}$)

Collector-Base cutoff current – Kollektor-Basis-Reststrom - $V_{CB} = 30\text{ V}$, (E open)	- I_{CBO}	–	–	100 nA
Emitter-Base-cutoff current – Emitter-Basis-Reststrom - $V_{EB} = 10\text{ V}$, (C open)	- I_{EBO}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz - $I_C = 5\text{ mA}$, - $V_{CE} = 30\text{ V}$, $f = 100\text{ MHz}$	f_T	–	220 MHz	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R_{thA}	< 420 K/W ¹⁾		



1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss